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PATENT ABSTRACTS OF JAPAN(21) Application number: **11055246**(51) Intl. Cl.: **B24D 3/32 B24B 37/00 B24D 7/00 H01L 21/304**(22) Application date: **03.03.99**

(30) Priority:	(71) Applicant: OKAMOTO MACHINE WORKS LTD
(43) Date of application publication: 12.09.00	(72) Inventor: YAMADA TSUTOMU KUBO TOMIO
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(54) POLISHING PAD

(57) Abstract:

PROBLEM TO BE SOLVED: To provide a CMP polishing pad excellent in heat resistance and providing a wafer excellent in thickness uniformity with small step difference between an insulating film and a metallic layer.

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SOLUTION: This polishing pad is used to polish a wafer by pressing the polishing pad to the wafer surface and rotating a spindle of a wafer chucking mechanism and a spindle of the polishing pad to slidngly rub the rotating polishing pad against the rotating wafer surface. In this case, a resin surface layer, slidngly rubbing against the wafer surface, of the polishing pad contains 5-50 wt.% of boehmite abrasive grain of 0.1 μm or less in grain diameter.

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